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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patentee: Ko, et al. Docket No.: TSM03-0615
Serial No.: 10/729,495 Art Unit: 2811
Patent No.: 7,112,495 B2 Issue Date: September 26, 2006
Filed: December 5, 2003 Examiner: Hung K. Vu
For: Structure and Method of a Strained Channel Transistor and a Second Semiconductor Component in an Integrated Circuit

Certificate of Corrections Branch
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Certificate
OCT 18 2006
of Correction

Request for Issuance of Certificate of Correction
Pursuant to 35 U.S.C. § 254 and 37 C.F.R. § 1.322

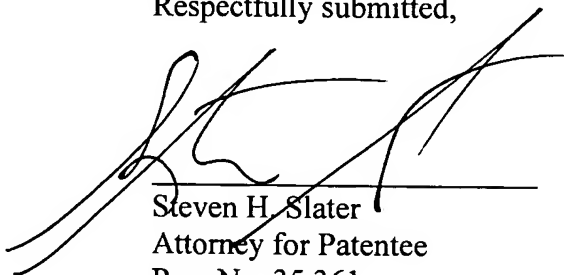
Dear Sir:

Upon review of the above-identified issued patent, Patentee notes errors in the patent that should be corrected as shown on the attached Certificate of Correction.

The mistakes noted on the attached Certificate of Correction were incurred through the fault of the Patent and Trademark Office. Accordingly, no fee is required.

Patentee respectfully solicits the issuance of the requested Certificate of Correction.

Respectfully submitted,


Steven H. Slater
Attorney for Patentee
Reg. No. 35,361

October 9, 2006
Date

SLATER & MATSIL, L.L.P.
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Suite 1000
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OCT 18 2006

**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**Page 1 of 1

PATENT NO. : 7,112,495 B2
APPLICATION NO. : 10/729,095
ISSUE DATE : September 26, 2006
INVENTOR(S) : Ko, *et al.*

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Page 2, Column 1, line 65; delete "6,872,810" insert --6,872,610--
Page 2, Column 2, line 27; delete "TEZUKA, T., et al., "High-Performance Strained Si-on-Insulator MOSFETs With Higher Strain in Si Channel Using Double SiGe Heterostructures," IEEE Transactions on Electron Devices, vol.49, No. 1, (Jan. 2002), pp.7-14." insert --TEZUKA, T., et al., "High-Performance Strained Si-on-Insulator MOSFETs by Novel Fabrication Processes Utilizing Ge-Condensation Technique," Symposium On VLSI Technology Digest of Technial Papers, (2002), pp. 96-97.--
Column 5, line 6; delete "patent application" insert --Patent Application--
Column 6, line 24; delete "suicides" insert --silicides--
Column 17, line 2; delete "cobalt suicide" insert --cobalt silicide--
Column 17, line 2; delete "nickel suicide" insert --nickel silicide--
Column 17, line 40; delete "suicide" insert --silicide--
Column 17, line 42; delete "stank" insert --stack--

MAILING ADDRESS OF SENDER(Please do not use customer number below):

Slater & Matsil, L.L.P.
17950 Preston Road, Suite 1000
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This collection of information is required by 37 CFR 1.322, 1.323, and 1.324. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 1.0 hour to complete, including gathering, preparing, and submitting the completed application for to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Attention Certificate of Corrections Branch, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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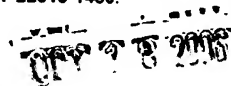
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Certificate of Mailing via First Class Mail (37 C.F.R. § 1.8(a))

Date of Deposit: October 9, 2006

I hereby certify that the below listed correspondence is being deposited with the United States Postal Service on the date indicated above as first class mail in an envelope addressed to: Certificate of Corrections Branch, Commissioner for Patents, P. O. Box 1450, Alexandria, VA 22313-1450.

Certificate of Mailing via First Class Mail (1 page)
Request for Issuance of Certificate of Correction (1 page)
Certificate of Correction (1 original and 1 copy)
Return Postcard

Respectfully submitted,

Michelle Reyes
Michelle Reyes
Legal Assistant

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